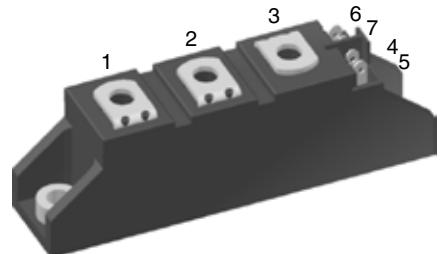


# Thyristor Modules

## Thyristor/Diode Modules

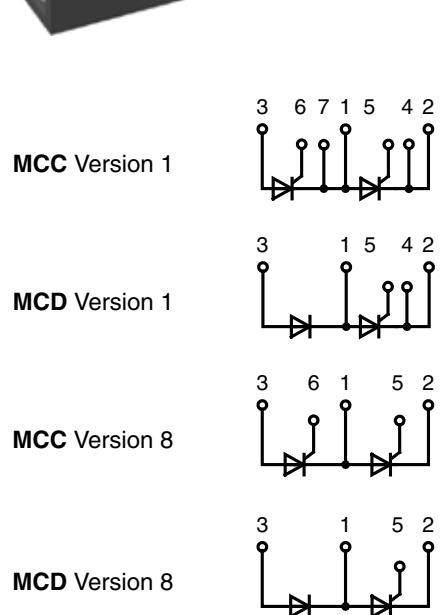
**I<sub>TRMS</sub>** = 2x 180 A  
**I<sub>TAVM</sub>** = 2x 116 A  
**V<sub>RRM</sub>** = 800-1800 V

V <sub>RSM</sub> V <sub>DSM</sub>	V <sub>RRM</sub> V <sub>DRM</sub>	Type	Version	1B	8B	Version	1B	8B
900	800	MCC 95-08	io1B / io8B			MCD 95-08	io1B / io8B	
1300	1200	MCC 95-12	io1B / io8B			MCD 95-12	io1B / io8B	
1500	1400	MCC 95-14	io1B / io8B			MCD 95-14	io1B / io8B	
1700	1600	MCC 95-16	io1B / io8B			MCD 95-16	io1B / io8B	
1900	1800	MCC 95-18	io1B / io8B			MCD 95-18	io1B / io8B	



Symbol	Conditions	Maximum Ratings		
I <sub>TRMS</sub> , I <sub>FRMS</sub>	T <sub>VJ</sub> = T <sub>VJM</sub>	180	A	
I <sub>TAVM</sub> ; I <sub>FAVM</sub>	T <sub>C</sub> = 85°C; 180° sine	116	A	
I <sub>TSM</sub> , I <sub>FSM</sub>	T <sub>VJ</sub> = 45°C V <sub>R</sub> = 0	t = 10 ms (50 Hz) t = 8.3 ms (60 Hz)	2250	A
	T <sub>VJ</sub> = T <sub>VJM</sub> V <sub>R</sub> = 0	t = 10 ms (50 Hz) t = 8.3 ms (60 Hz)	2400	A
	T <sub>VJ</sub> = T <sub>VJM</sub> V <sub>R</sub> = 0	t = 10 ms (50 Hz) t = 8.3 ms (60 Hz)	2000	A
	T <sub>VJ</sub> = T <sub>VJM</sub> V <sub>R</sub> = 0	t = 10 ms (50 Hz) t = 8.3 ms (60 Hz)	2150	A
I <sup>2</sup> t	T <sub>VJ</sub> = 45°C V <sub>R</sub> = 0	t = 10 ms (50 Hz) t = 8.3 ms (60 Hz)	25 300	A <sup>2</sup> s
	T <sub>VJ</sub> = T <sub>VJM</sub> V <sub>R</sub> = 0	t = 10 ms (50 Hz) t = 8.3 ms (60 Hz)	23 900	A <sup>2</sup> s
	T <sub>VJ</sub> = T <sub>VJM</sub> V <sub>R</sub> = 0	t = 10 ms (50 Hz) t = 8.3 ms (60 Hz)	20 000	A <sup>2</sup> s
	T <sub>VJ</sub> = T <sub>VJM</sub> V <sub>R</sub> = 0	t = 10 ms (50 Hz) t = 8.3 ms (60 Hz)	19 100	A <sup>2</sup> s
(di/dt) <sub>cr</sub>	T <sub>VJ</sub> = T <sub>VJM</sub> f = 50 Hz; t <sub>p</sub> = 200 µs;	repetitive, I <sub>T</sub> = 250 A	150	A/µs
	V <sub>D</sub> = 2/3 V <sub>DRM</sub> I <sub>G</sub> = 0.45 A	non repetitive, I <sub>T</sub> = I <sub>TAVM</sub>	500	A/µs
	di <sub>G</sub> /dt = 0.45 A/µs			
(dv/dt) <sub>cr</sub>	T <sub>VJ</sub> = T <sub>VJM</sub> ; V <sub>D</sub> = 2/3 V <sub>DRM</sub> R <sub>GK</sub> = ∞; method 1 (linear voltage rise)		1000	V/µs
P <sub>GM</sub>	T <sub>VJ</sub> = T <sub>VJM</sub> ; t <sub>p</sub> = 30 µs I <sub>T</sub> = I <sub>T(AV)M</sub> ; t <sub>p</sub> = 500 µs		10	W
			5	W
P <sub>GAV</sub>			0.5	W
V <sub>RGM</sub>			10	V
T <sub>VJ</sub>			-40...+125	°C
T <sub>VJM</sub>			125	°C
T <sub>stg</sub>			-40...+125	°C
V <sub>ISOL</sub>	50/60 Hz, RMS	t = 1 min	3000	V~
	I <sub>ISOL</sub> ≤ 1 mA	t = 1 s	3600	V~
M <sub>d</sub>	Mounting torque (M5)		2.5 - 4	Nm
	Terminal connection torque (M5)		2.5 - 4	Nm
Weight	Typical including screws		85	g

Data according to IEC 60747 and refer to a single diode unless otherwise stated.



### Features

- International standard package, JEDEC TO-240 AA
- Direct copper bonded Al<sub>2</sub>O<sub>3</sub> -ceramic base plate
- Planar passivated chips
- Isolation voltage 3600 V~
- UL registered, E 72873
- Gate-cathode twin pins for version 1

### Applications

- DC Motor control
- Softstart AC motor controller
- Light, heat and temperature control

### Advantages

- Space and weight savings
- Simple mounting with two screws
- Improved temperature & power cycling
- Reduced protection circuits

Symbol	Conditions	Characteristic Values	
		typ.	max.
$I_{RRM}, I_{DRM}$	$V_R / V_D = V_{RRM} / V_{DRM}$	$T_{VJ} = T_{VJM}$	5 mA
$V_T, V_F$	$I_T / I_F = 300 \text{ A}$	$T_{VJ} = 25^\circ\text{C}$	1.5 V
$V_{TO}$	For power-loss calculations only		0.8 V
$r_t$		$T_{VJ} = T_{VJM}$	2.4 mΩ
$V_{GT}$	$V_D = 6 \text{ V}$	$T_{VJ} = 25^\circ\text{C}$	2.5 V
		$T_{VJ} = -40^\circ\text{C}$	2.6 V
$I_{GT}$	$V_D = 6 \text{ V}$	$T_{VJ} = 25^\circ\text{C}$	150 mA
		$T_{VJ} = -40^\circ\text{C}$	200 mA
$V_{GD}$	$V_D = \frac{2}{3} V_{DRM};$	$T_{VJ} = T_{VJM}$	0.2 V
$I_{GD}$			10 mA
$I_L$	$t_p = 10 \mu\text{s}; V_D = 6 \text{ V}$ $I_G = 0.45 \text{ A}; dI_G/dt = 0.45 \text{ A}/\mu\text{s}$	$T_{VJ} = 25^\circ\text{C}$	450 mA
$I_H$	$V_D = 6 \text{ V}; R_{GK} = \infty;$	$T_{VJ} = 25^\circ\text{C}$	200 mA
$t_{gd}$	$V_D = \frac{1}{2} V_{DRM}$ $I_G = 0.45 \text{ A}; dI_G/dt = 0.45 \text{ A}/\mu\text{s}$	$T_{VJ} = 25^\circ\text{C}$	2 μs
$t_q$	$V_D = \frac{2}{3} V_{DRM}$ $dv/dt = 20 \text{ V}/\mu\text{s}; -di/dt = 10 \text{ A}/\mu\text{s}$ $I_T = 150 \text{ A}; V_R = 100 \text{ V}; t_p = 200 \mu\text{s}$	$T_{VJ} = T_{VJM}$	185 μs
$Q_s$	$I_T / I_F = 50 \text{ A}; -di/dt = 6 \text{ A}/\mu\text{s}$	$T_{VJ} = T_{VJM}$	170 μC
$I_{RM}$			45 A
$R_{thJC}$	per thyristor; DC current		0.22 K/W
	per module		0.11 K/W
$R_{thJK}$	per thyristor; DC current		0.42 K/W
	per module		0.21 K/W
$d_s$	Creeping distance on surface		12.7 mm
$d_A$	Creepage distance in air		9.6 mm
$a$	Maximum allowable acceleration		50 m/s <sup>2</sup>

## Optional accessories for modules

Coded gate/cathode twin plugs with wire length = 350 mm, gate = yellow, cathode = red

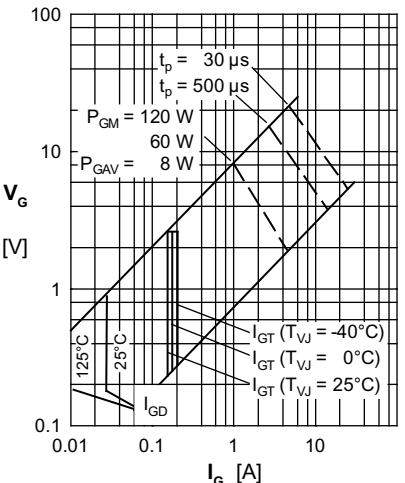
Type **ZY 200L** (L = Left for pin pair 4/5) UL 758, style 1385,Type **ZY 200R** (R = Right for pin pair 6/7) CSA class 5851, guide 460-1-1

Fig. 1 Gate trigger characteristics

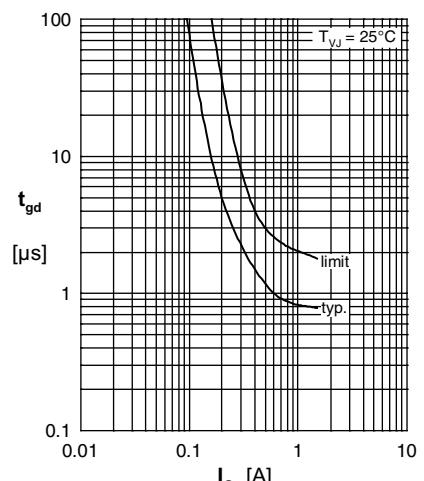
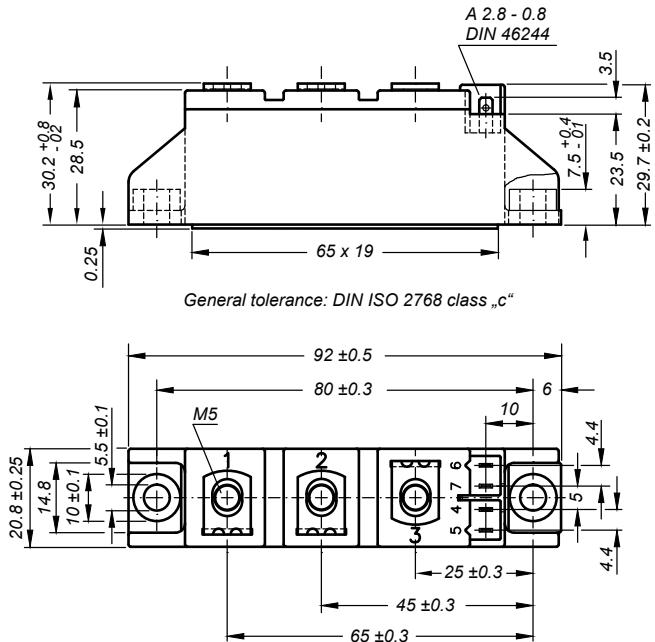


Fig. 2 Gate trigger delay time

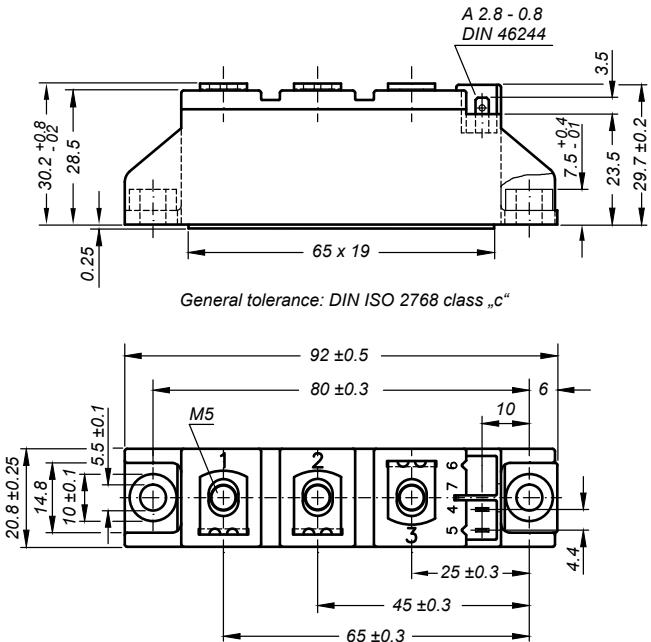
Dimensions in mm (1 mm = 0.0394")

## MCC... Version 1B



Optional accessories: Keyed gate/cathode twin plugs  
 Wire length: 350 mm, gate = yellow, cathode = red  
 UL 758, style 1385, CSA class 5851, guide 460-1-1  
 Type ZY 200L (L = Left for pin pair 4/5)  
 Type ZY 200R (R = Right for pin pair 6/7)

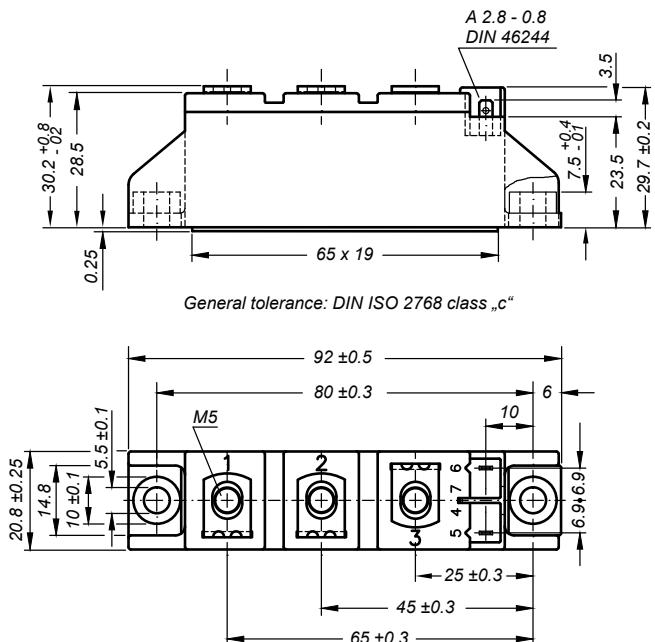
## MCD... Version 1B



General tolerance: DIN ISO 2768 class „c“

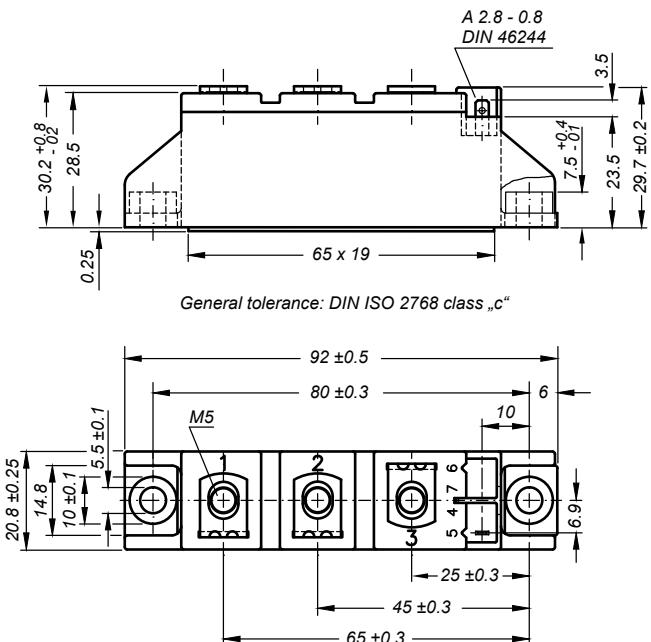
Optional accessories: Keyed gate/cathode twin plugs  
 Wire length: 350 mm, gate = yellow, cathode = red  
 UL 758, style 1385, CSA class 5851, guide 460-1-1  
 Type ZY 200L (L = Left for pin pair 4/5)

## MCC... Version 8B



General tolerance: DIN ISO 2768 class „c“

## MCD... Version 8B



General tolerance: DIN ISO 2768 class „c“

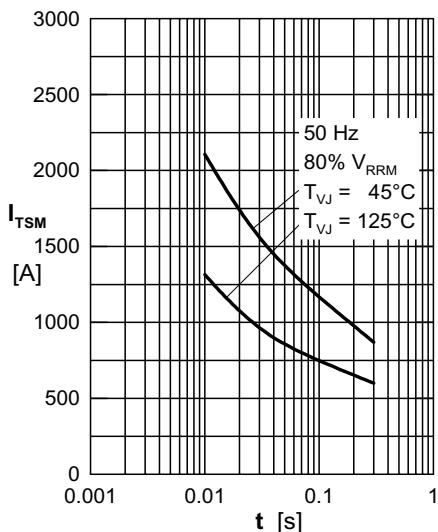


Fig. 3 Surge overload current  $I_{TSM}$ ,  
 $I_{FSM}$ : Crest value, t: duration

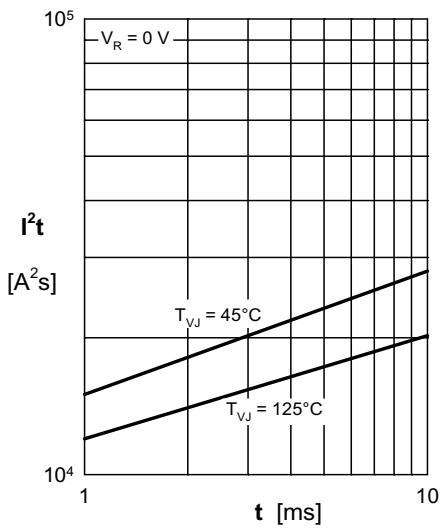


Fig. 4  $I^2t$  versus time (1-10 ms)

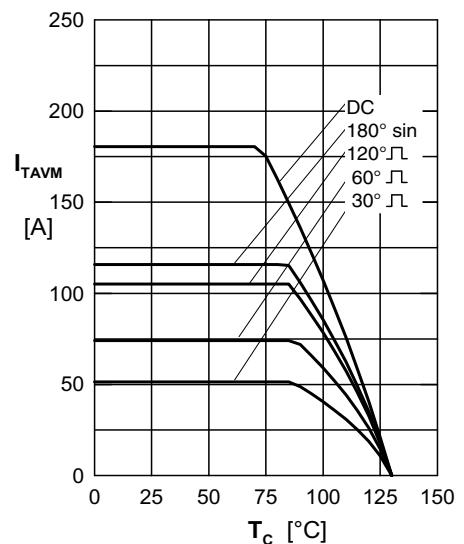


Fig. 4a Maximum forward current at case temperature

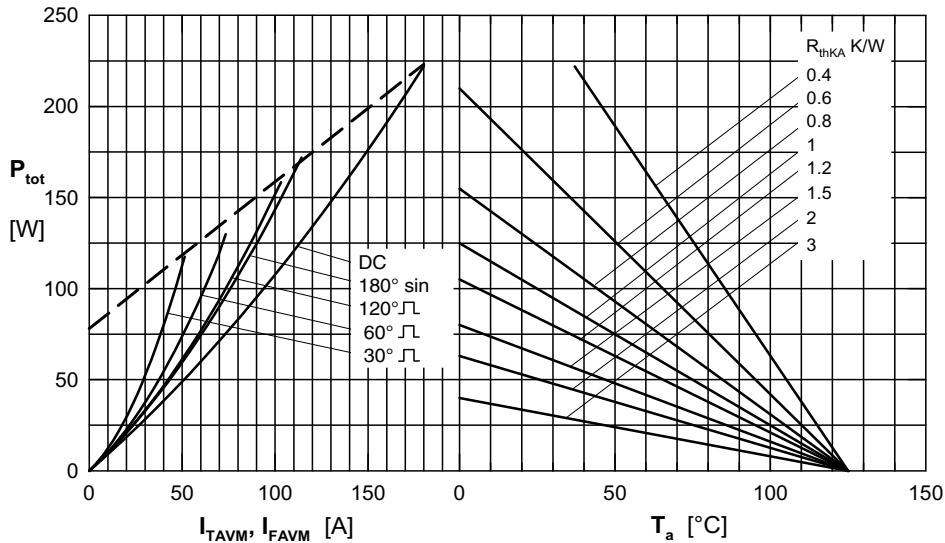


Fig. 5 Power dissipation versus on-state current & ambient temperature (per thyristor or diode)

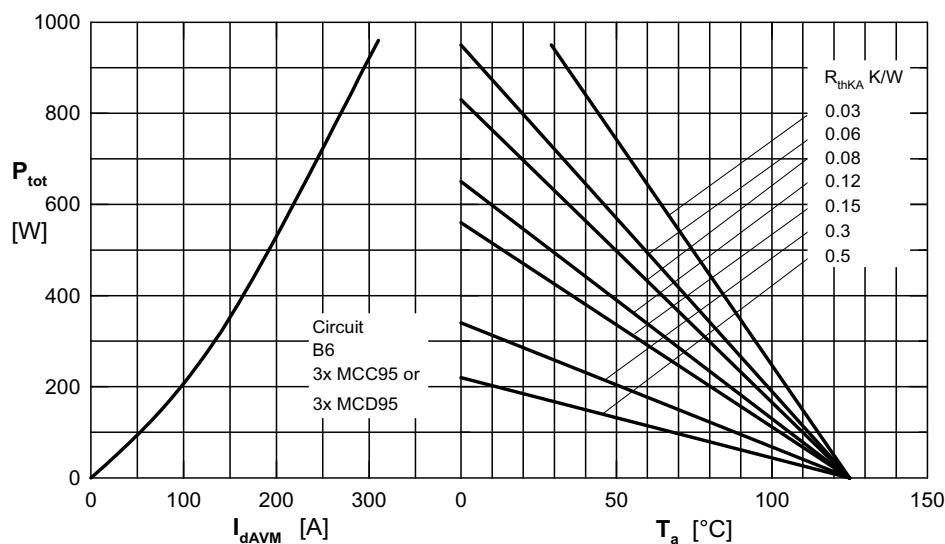


Fig. 6 Three phase rectifier bridge:  
Power dissipation vs. direct output current and ambient temperature

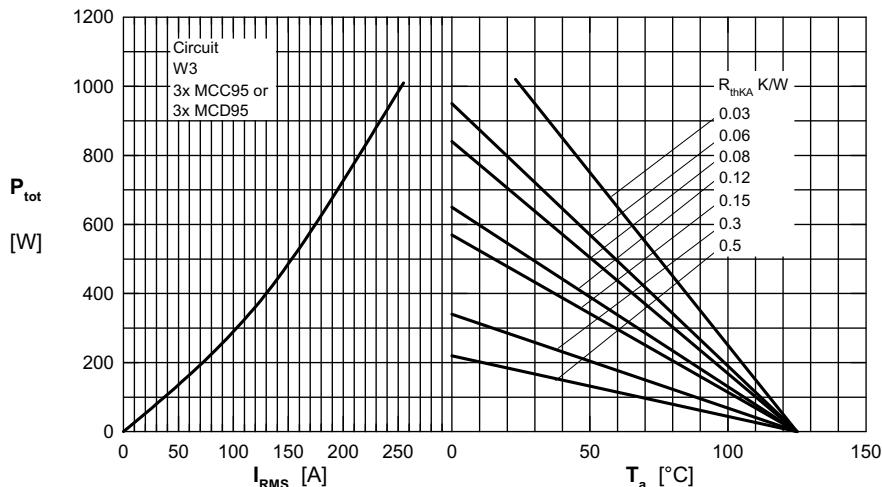


Fig. 7 Three phase AC-controller:  
Power dissipation versus RMS  
output current and ambient  
temperature

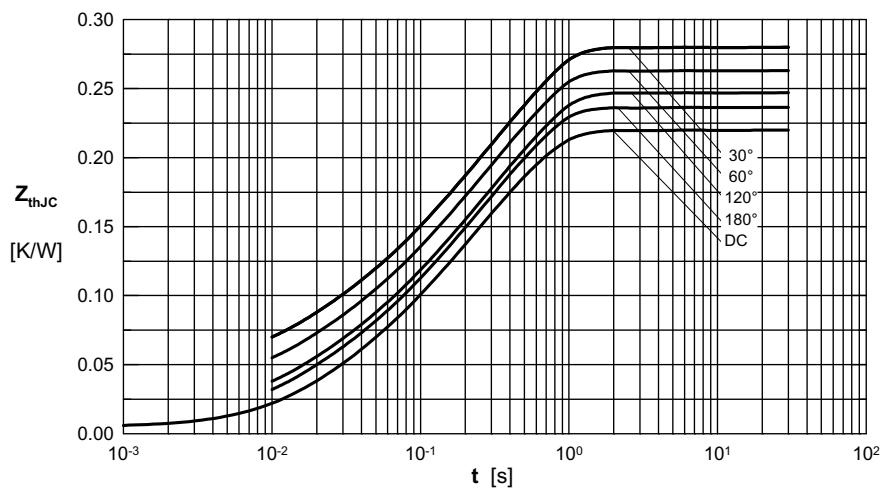


Fig. 8 Transient thermal impedance  
junction to case  
(per thyristor or diode)

d	$R_{thJC}$ (K/W)
DC	0.22
180°	0.23
120°	0.25
60°	0.27
30°	0.28

Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.0066	0.0019
2	0.0678	0.0477
3	0.1456	0.344

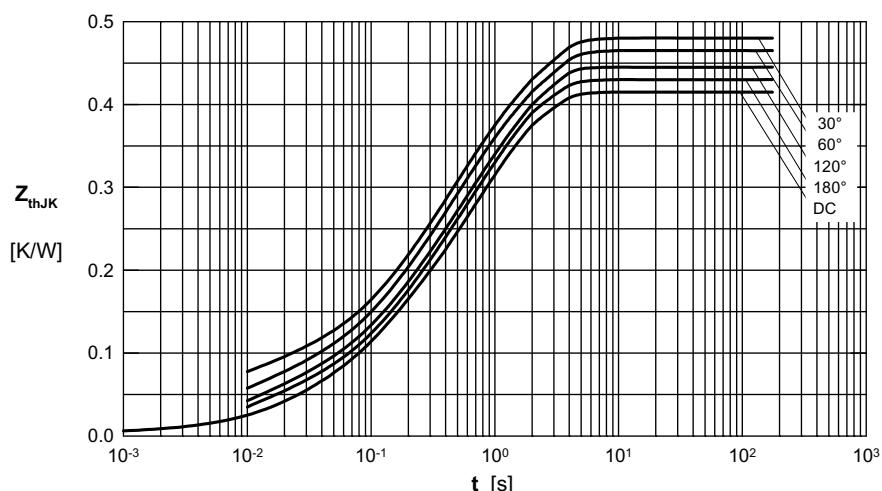


Fig. 9 Transient thermal impedance  
junction to heatsink  
(per thyristor or diode)

d	$R_{thJK}$ (K/W)
DC	0.42
180°	0.43
120°	0.45
60°	0.47
30°	0.48

Constants for  $Z_{thJK}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.0066	0.0019
2	0.0678	0.0477
3	0.1456	0.344
4	0.2	1.32